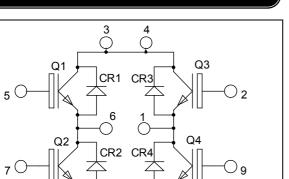
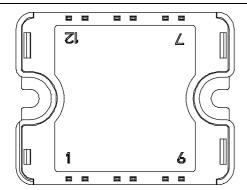


## Full - Bridge Trench + Field Stop IGBT3 Power Module



10

12



NTC

Pins 3/4 must be shorted together

## $V_{CES} = 600V$ $I_C = 30A$ @ Tc = 80°C

#### **Application**

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
  - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

#### **Benefits**

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

### Absolute maximum ratings

11

| Symbol    | Parameter                                   |                                  | Max ratings | Unit |
|-----------|---------------------------------------------|----------------------------------|-------------|------|
| $V_{CES}$ | Collector - Emitter Breakdown Voltage       |                                  | 600         | V    |
| Ţ         | Continuous Collector Current                | $T_C = 25^{\circ}C$              | 50          |      |
| 1C        | I <sub>C</sub> Continuous Collector Current | $T_C = 80$ °C                    | 30          | Α    |
| $I_{CM}$  | Pulsed Collector Current                    | $T_C = 25^{\circ}C$              | 60          |      |
| $V_{GE}$  | Gate – Emitter Voltage                      |                                  | ±20         | V    |
| $P_{D}$   | Maximum Power Dissipation                   | $T_C = 25^{\circ}C$              | 90          | W    |
| RBSOA     | Reverse Bias Safe Operating Area            | $T_{\rm J} = 150^{\circ}{\rm C}$ | 60A @ 550V  |      |

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

| Symbol        | Characteristic                       | Test Conditions                    |                     | Min | Typ | Max | Unit |
|---------------|--------------------------------------|------------------------------------|---------------------|-----|-----|-----|------|
| $I_{CES}$     | Zero Gate Voltage Collector Current  | $V_{GE} = 0V, V_{CE} = 600V$       |                     |     |     | 250 | μΑ   |
| V             | Collector Emitter Saturation Voltage | $V_{GE} = 15V$                     | $T_j = 25^{\circ}C$ |     | 1.5 | 1.9 | V    |
| $V_{CE(sat)}$ | Conector Emitter Saturation Voltage  | $I_C = 30A$ $T_j = 150^{\circ}C$   |                     | 1.7 |     | v   |      |
| $V_{GE(th)}$  | Gate Threshold Voltage               | $V_{GE} = V_{CE}, I_C = 400 \mu A$ |                     | 5.0 | 5.8 | 6.5 | V    |
| $I_{GES}$     | Gate – Emitter Leakage Current       | $V_{GE} = 20V, V_{CE} = 0V$        |                     |     |     | 300 | nA   |

### **Dynamic Characteristics**

| Symbol         | Characteristic                                   | Test Conditions                                                                                  |                        | Min  | Typ  | Max  | Unit |
|----------------|--------------------------------------------------|--------------------------------------------------------------------------------------------------|------------------------|------|------|------|------|
| Cies           | Input Capacitance                                | $V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$                                                          |                        |      | 1600 |      |      |
| Coes           | Output Capacitance                               |                                                                                                  |                        |      | 110  |      | pF   |
| $C_{res}$      | Reverse Transfer Capacitance                     |                                                                                                  |                        |      | 50   |      |      |
| $T_{d(on)}$    | Turn-on Delay Time                               | Inductive Switching (25°C)                                                                       |                        |      | 110  |      |      |
| T <sub>r</sub> | Rise Time                                        | $V_{GE} = \pm 15V$                                                                               |                        |      | 45   |      |      |
| $T_{d(off)}$   | Turn-off Delay Time                              | $ \begin{array}{l} V_{Bus} = 300V \\ I_C = 30A \\ R_G = 10\Omega \end{array} $                   |                        |      | 200  |      | ns   |
| $T_{\rm f}$    | Fall Time                                        |                                                                                                  |                        |      | 40   |      |      |
| $T_{d(on)}$    | Turn-on Delay Time                               | Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_{C} = 30A$ $R_{G} = 10\Omega$ |                        |      | 120  |      | ns   |
| $T_{\rm r}$    | Rise Time                                        |                                                                                                  |                        |      | 50   |      |      |
| $T_{d(off)}$   | Turn-off Delay Time                              |                                                                                                  |                        |      | 250  |      |      |
| $T_{\rm f}$    | Fall Time                                        |                                                                                                  |                        |      | 60   |      |      |
| Eon            | Turn-on Switching Energy $V_{GE} = \pm 15V_{GE}$ | $V_{GE} = \pm 15V$                                                                               | $T_j = 25^{\circ}C$    |      | 0.16 |      | mJ   |
| Lon            | Turn-on Switching Energy                         | $V_{\text{Bus}} = 300 \text{V}$                                                                  | $T_{j} = 150^{\circ}C$ |      | 0.3  |      | 1113 |
| E-ec           | E Turn off Switching Energy                      | $I_C = 30A$                                                                                      | $T_j = 25^{\circ}C$    |      | 0.7  |      | mJ   |
| Loff           |                                                  | $R_G = 10\Omega$ $T_j = 150$ °C                                                                  |                        | 1.05 |      | 1113 |      |

## Reverse diode ratings and characteristics

| Symbol      | Characteristic                          | Test Conditions                                                | Test Conditions                  |               | Тур  | Max | Unit |   |
|-------------|-----------------------------------------|----------------------------------------------------------------|----------------------------------|---------------|------|-----|------|---|
| $V_{RRM}$   | Maximum Peak Repetitive Reverse Voltage |                                                                |                                  | 600           |      |     | V    |   |
| $I_{RM}$    | Maximum Reverse Leakage Current         | V <sub>R</sub> =600V                                           | $T_j = 25$ °C                    |               |      | 250 | μA   |   |
| 1RM         |                                         | VR OOOV                                                        | $T_j = 150$ °C                   |               |      | 500 | μΛ   |   |
| $I_F$       | DC Forward Current                      |                                                                | Tc = 80°C                        |               | 30   |     | A    |   |
| $V_{\rm F}$ | Diode Forward Voltage                   | $I_F = 30A$ $V_{GE} = 0V$                                      | $T_i = 25^{\circ}C$              |               | 1.6  | 2   | V    |   |
| V F         | Diode Forward Voltage                   |                                                                | $T_{i} = 150^{\circ}C$           |               | 1.5  |     |      |   |
| $t_{rr}$    | Rayarsa Racovary Tima                   | Recovery Time $ T_{j} = 25^{\circ}C $ $ T_{j} = 150^{\circ}C $ | $T_j = 25$ °C                    |               | 100  |     | ns   |   |
| ٠rr         | Reverse Recovery Time                   |                                                                | $T_j = 150$ °C                   |               | 150  |     | 113  |   |
| 0           | O Payanga Pagayany Changa               |                                                                | $I_F = 30A$                      | $T_j = 25$ °C |      | 1.5 |      | C |
| $Q_{rr}$    | Reverse Recovery Charge                 | $di/dt = 1800 \text{A}/\mu\text{s}$                            | $T_{i} = 150^{\circ}C$           |               | 3.1  |     | μC   |   |
| Б           | В                                       |                                                                | $T_j = 25$ °C                    |               | 0.34 |     | mJ   |   |
| $E_{r}$     | Reverse Recovery Energy                 |                                                                | $T_{\rm j} = 150^{\circ}{\rm C}$ |               | 0.75 |     | 111J |   |

2 - 6



### Thermal and package characteristics

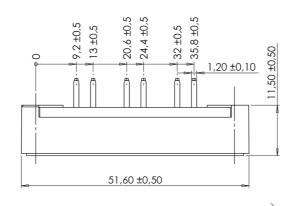
| Symbol      | Characteristic                                                 |             |     | Min  | Тур  | Max | Unit |
|-------------|----------------------------------------------------------------|-------------|-----|------|------|-----|------|
| $R_{thJC}$  | Junction to Case Thermal Resistance                            | IGBT        |     |      | 1.6  | °C/ |      |
| KthJC       |                                                                | Diode       |     |      | 2.45 | W   |      |
| $V_{ISOL}$  | RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz |             |     | 4000 |      |     | V    |
| $T_{J}$     | Operating junction temperature range                           |             | -40 |      | 175  |     |      |
| $T_{STG}$   | Storage Temperature Range                                      |             |     | -40  |      | 125 | °C   |
| $T_{\rm C}$ | Operating Case Temperature                                     |             |     | -40  |      | 100 |      |
| Torque      | Mounting torque                                                | To heatsink | M4  | 2    |      | 3   | N.m  |
| Wt          | Package Weight                                                 |             |     |      | 80   | g   |      |

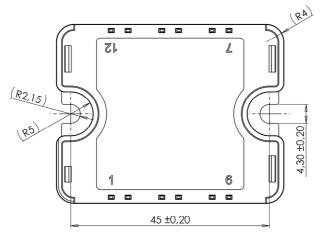
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

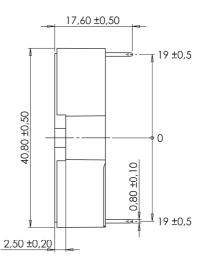
| Symbol          | Characteristic              | Min | Typ  | Max | Unit |
|-----------------|-----------------------------|-----|------|-----|------|
| R <sub>25</sub> | Resistance @ 25°C           |     | 50   |     | kΩ   |
| B 25/85         | $T_{25} = 298.15 \text{ K}$ |     | 3952 |     | K    |

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature}$$
 
$$R_T: \text{ Thermistor value at T}$$

### SP1 Package outline (dimensions in mm)



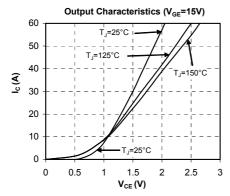


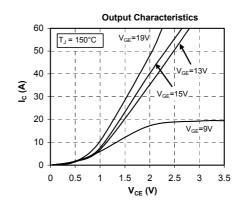


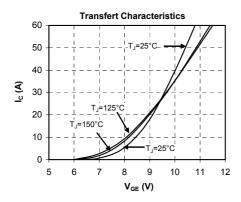
See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

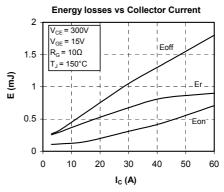


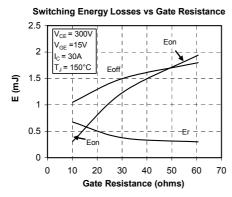
### **Typical Performance Curve**

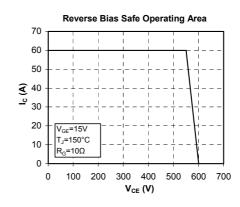


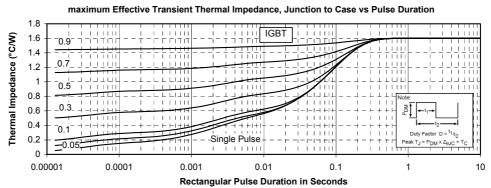




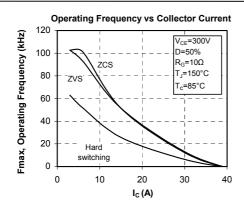


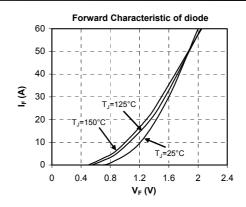


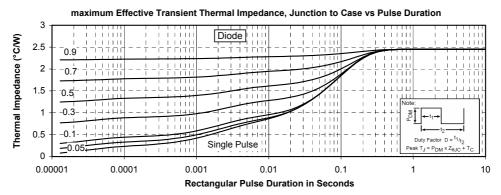












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